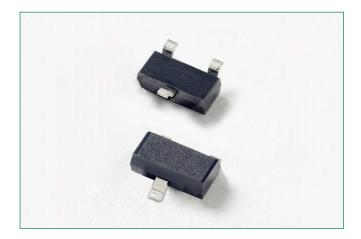
Thyristors Datasheet

SxX8BBS Series EV Series 0.8 Amp Sensitive SCRs

RoHS



Main Features

Symbol	Value	Unit
I _{T(RMS)}	0.8	А
$V_{\rm drm}/V_{\rm rrm}$	600	V
Ι _{GT}	200	μΑ

Description

This new sensitive SCR component series offers 600V $\mathrm{V}_{_{\mathrm{DRM}}}$ and 0.8A $I_{\text{T(RMS)}}$ capability in the smallest package size in the industry, SOT23. It is specifically designed for GFCI (Ground Fault Circuit Interrupter) applications. All SCRs junctions are glass-passivated to ensure long term reliability and parametric stability.

Features

- Very compact SOT23 SMT package
- Surge current capability up to 12A @ 60Hz
- Blocking voltage (V_{DRM} / V_{RRM}) capability - up to 600V
- High dv/dt noise immunity
- Improved turn-off time (t_a) <</p> 25 µsec
- Sensitive gate for direct microprocessor interface
- RoHS compliant and Halogen-Free

Applications

The SxX8BBS series is specifically designed for GFCI (Ground Fault Circuit Interrupter) and applications.

Schematic Symbol G $^{\circ}$ KO -OA

Pin out Anode 1 2 Cathode Gate

Absolute Maximum Ratings

Symbol	Parameter	Value	Unit		
$V_{\rm DSM}/V_{\rm RSM}$	Peak non-repetitive blocking voltage	Pw=100µs		700	V
I _{T(RMS)}	RMS on-state current (full sine wave)		$T_c = 80^{\circ}C$	0.8	А
I _{T(AV)}	Average on-state current		$T_c = 80^{\circ}C$	0.51	А
1	Non repetitive surge peak on-state current		f= 50Hz	10	А
I _{TSM}	(Single cycle, T_j initial = 25°C)		f= 60Hz	12	А
l ² t	I ² t Value for fusing	$t_p = 10 \text{ ms}$	f= 50 Hz	0.5	A²s
11	i t value for fusing	$t_{p} = 8.3 \text{ ms}$	f= 60 Hz	0.6	A²s
di/dt	Critical rate of rise of on-state current $\rm I_{g}$ = 10mA	60 Hz	$T_{J} = 125^{\circ}C$	80	A/µs
I _{GM}	Peak Gate Current	$t_p = 20 \ \mu s$	$T_{J} = 125^{\circ}C$	1.0	А
P _{G(AV)}	Average gate power dissipation		$T_{J} = 125^{\circ}C$	0.1	W
T _{stg}	Storage junction temperature range			-40 to 150	°C
TJ	Operating junction temperature range			-40 to 125	°C



Electrical Characteristics	(Т	_	25°C	unless	otherwise	specified)
	11	_ =	ZO C,	uniess	other wise	specified)

Symbol	Description	Test Conditions	Limit	Value	Unit
1	DC Cata Trigger Current	\/6\/R100_O	MIN.	50	μA
I _{GT}	DC Gate Trigger Current	$V_{_{\mathrm{D}}}$ = 6V, $\mathrm{R}_{_{\mathrm{L}}}$ = 100 Ω	MAX.	200	μA
V _{GT}	DC Gate Trigger Voltage	$V_{_{ m D}}$ = 6V, $R_{_{ m L}}$ = 100 Ω	MAX.	0.8	V
V _{GRM}	Peak Reverse Gate Voltage	$I_{RG} = 10 \mu A$	MIN.	8	V
I _H	Holding Current	Initial Current = 20mA	MAX.	10	mA
(dv/dt)s	Critical Rate-of-Rise of Off-State Voltage	$T_{J} = 125^{\circ}C$ $V_{D} = 67\%V_{DRM}/V_{RRM}$ Exp. Waveform, $R_{GK} = 1 k\Omega$	MIN.	50	V/µs
V_{gD}	Gate Non-Trigger Voltage		MIN.	0.2	V
t _q	Turn-Off Time	I _T =0.5A	MAX.	25	μs
t _{gt}	Turn-On Time	I _g =10mA,Pw= 15μsec, I _T = 1.6A(pk)	TYP.	2.0	μs

Static Characteristics ($T_1 = 25^{\circ}$ C, unless otherwise specified)

Symbol	Description	Test Conditions	Limit	Value	Unit
V _{TM}	Peak On-State Voltage	$I_{TM} = 1.6A (pk)$	MAX.	1.70	V
1 /1		$T_{J} = 25^{\circ}C$	MAX.	5	μΑ
DRM ^{/ I} RRM		$T_{J} = 125^{\circ}C$	MAX.	100	μΑ

Thermal Resistances

Symbol	Description	Value	Unit
R _{e(JC)}	Junction to case (AC)	45	°C/W
R _{e(J-A)}	Junction to ambient	220	°C/W



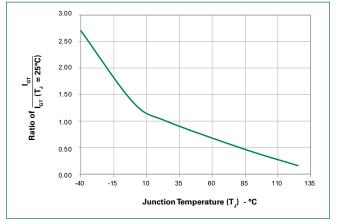
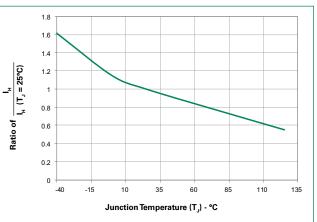


Figure 2: Normalized DC Holding Current vs. Junction Temperature



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SxX8BBS Series EV Series 0.8 Amp Sensitive SCRs

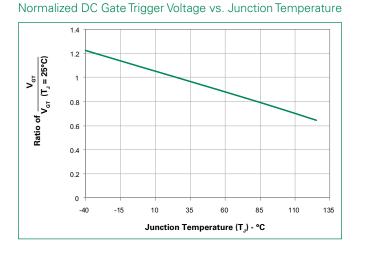


Figure 3:

Figure 4: On-State Current vs. On-State Voltage (Typical)

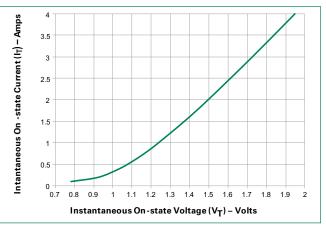


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

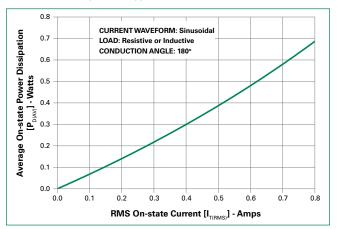
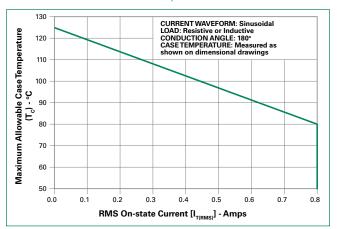
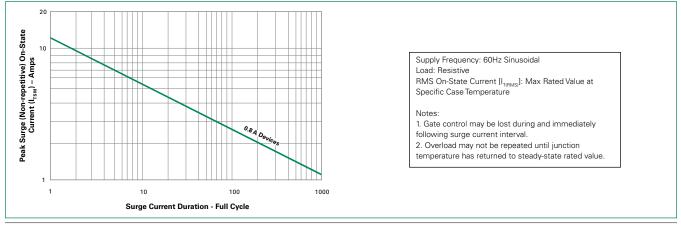


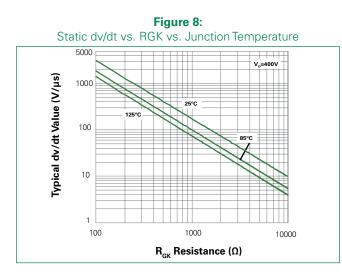
Figure 6: Maximum Allowable Case Temperature vs. On-State Current

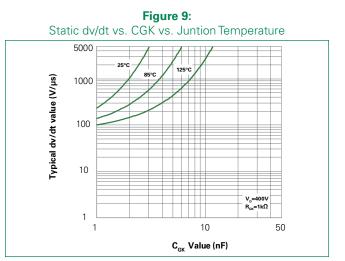






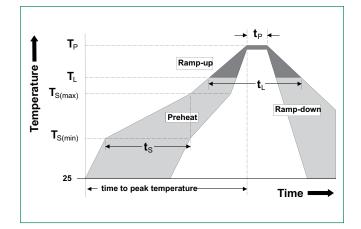
SxX8BBS Series EV Series 0.8 Amp Sensitive SCRs





Soldering Parameters

Reflow Condition		Pb – Free assembly
	- Temperature Min (T _{s(min)})	150°C
Pre Heat	- Temperature Max (T _{s(max)})	200°C
	- Time (min to max) (t _s)	60 - 120 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		3°C/second max
$T_{S(max)}$ to T_L - F	Ramp-up Rate	5°C/second max
Reflow	- Temperature (T _L) (Liquidus)	217°C
nellow	- Time (min to max) (t _s)	60 – 150 seconds
Peak Tempera	ature (T _P)	260 ^{+0/-5} °C
Time within	5°C of actual peak Temperature (t _p)	30 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T _P)		8 minutes Max.
Do not excee	d	260°C



SxX8BBS Series EV Series 0.8 Amp Sensitive SCRs

Physical Specifications

Terminal Finish	100% Matte Tin-plated.
Body Material	UL Recognized compound meeting flammability rating V-0.
Lead Material	Copper Alloy

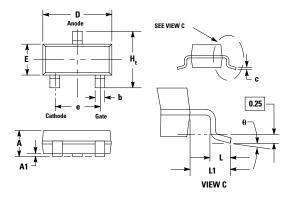
Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

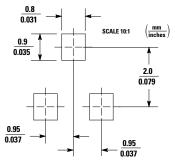
Reliability/Environmental Tests

Test	Specifications and Conditions
HTRB (AC Blocking)	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ $\rm V_{\rm DRM}$ @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -55°C to +150°C; 15-min dwell-time
H3TRB	EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C; 85% rel humidity
UHAST	ESD22-A118, 96hours, 130°C, 85%RH
Resistance to Solder Heat	MIL-STD-750 Method 2031, 260°C, 10s
Solderability	ANSI/J-STD-002, category 3, Test A
Moisture Sensitivity Level	Level 1, JEDEC-J-STD-020D

Dimensions – SOT-23



SOLDERING FOOTPRINT



Dimensions		Inches		r	Villimeter	s
Dimensions	Min	Тур	Max	Min	Тур	Max
Α	0.04	0.04	0.04	0.89	1.02	1.12
A1	0.00	0.00	0.01	0.01	0.10	0.15
b	0.02	0.02	0.02	0.38	0.46	0.51
C	0.00	0.01	0.01	0.08	0.13	0.18
D	0.11	0.11	0.12	2.80	2.90	3.04
Е	0.05	0.05	0.06	1.19	1.30	1.40
е	0.07	0.08	0.08	1.78	1.91	2.06
L	0.02	0.02	0.02	0.40	0.49	0.60
L1	0.01	0.02	0.03	0.36	0.53	0.74
н	0.08	0.09	0.10	2.10	2.30	2.64
θ	0°	-	10°	0°	-	10°

Packing Options

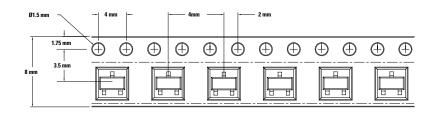
Part Number	Marking	Weight	Packing Mode	Base Quantity
S6X8BBSRP	6X8	0.01g	Tape & Reel	3000

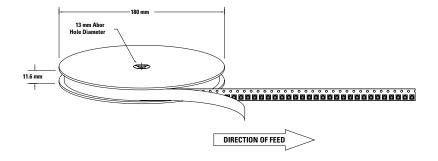
Product Selector

Part Number	Voltage 600V	Gate Sensitivity	Package
S6X8BBS	Х	200 µA	SOT-23

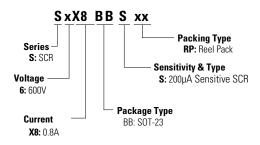


SOT-23 Reel Pack (RP) Specifications

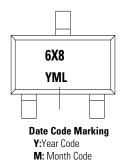




Part Numbering System



Part Marking System



L: Location Code

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